



UM9441

PIN RADIATION DETECTORS

DESCRIPTION

Description

Silicon PIN devices are effective detectors of nuclear and electromagnetic radiation. This includes gamma radiation, electrons, and X-rays. The detectors can be used across the temperature range of -55 °C to +175 °C instead of being restricted to use at low temperatures.

The absorbed radiation produces electron-hole pairs in the space charge region. These charges are swept out by the applied field and result in a current flow proportional to the rate of absorbed radiation.

The Microsemi UM9441 series utilizes high resistivity material and is designed to have a uniform area mesa structure to define the active volume. The current sensitivity of this device is proportional only to the I-region volume and is independent of

temperature so long as applied voltage exceeds the saturation voltage. This structure also minimizes the effects of permanent damage caused by neutrons and other high energy radiation. Experiments on devices of the UM9441 design show no degradation in gamma sensitivity resulting from a total dose of 10^{14} neutrons/cm² of 1 MeV equivalent.

Package

The UM9441 is an axially leaded device constructed by metallurgically bonding the PIN chip in between two molybdenum refractory pins that are typically 0.125 inches in diameter and 0.050 inches long. Hyper-pure glass is then fused over this bond to form a void less seal. Leads are then brazed to ends of molybdenum pins. This results in a high-reliability package using materials so well thermally matched that the UM9441 can withstand temperature shock or cycling from -196 °C to +300 °C.

KEY FEATURES

- High Photocurrent Sensitivity
- High Reliability Construction
- Fast Rise Time
- Wide Dynamic Range
- Hardness to Neutron Bombardment
- Low operating Voltage

APPLICATIONS/BENEFITS

- Surface Mount package available
- RoHS compliant devices available

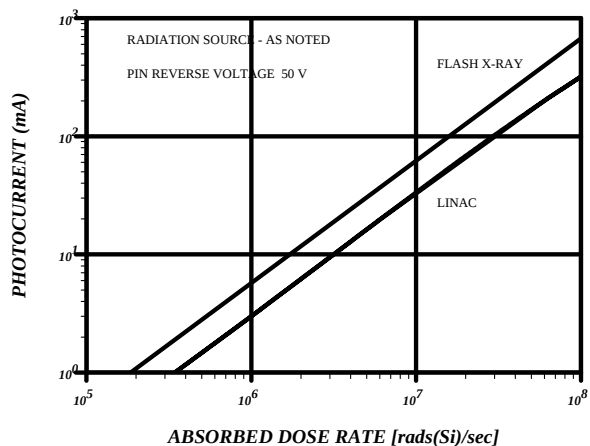
IMPORTANT: For the most current data, consult MICROSEMI's website: <http://www.microsemi.com>

ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)

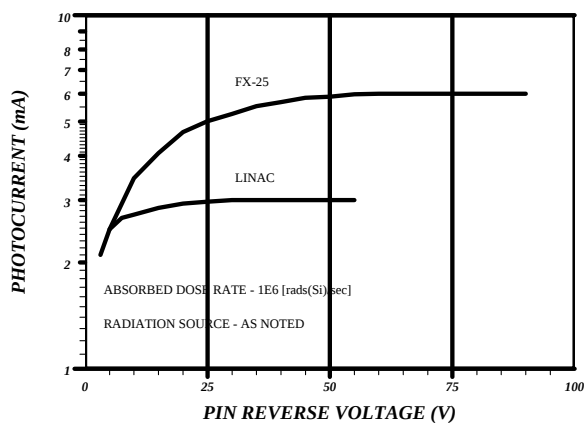
Rating	Symbol	Value	Unit
Reverse Voltage	V _R	100	V
Photocurrent		3Adc	3A ² s pulsed
Storage Temperature	T _{stg}	-55 to +200	°C
Operating Temperature	T _{op}	-55 to +175	°C

Parameter	Conditions	Min	Typ.	Max	Units
Photocurrent	$V_R = 50\text{ V}$ 10^6 rads(Si)/sec 2.5 MeV Flash X-Ray Ion Physics Corporation FX-25	4.0	6.0		mA
Capacitance	$F = 1\text{ MHz}$, $V = 50\text{ V}$			10	pF
Reverse Current	$V_R = 50\text{ V}$			1.0	μA
Minority Carrier Lifetime	$I_F = 10\text{ mA}$	2.0			μs

**PHOTOCURRENT SENSITIVITY
TYPICAL**



**VOLTAGE SENSITIVITY
TYPICAL**





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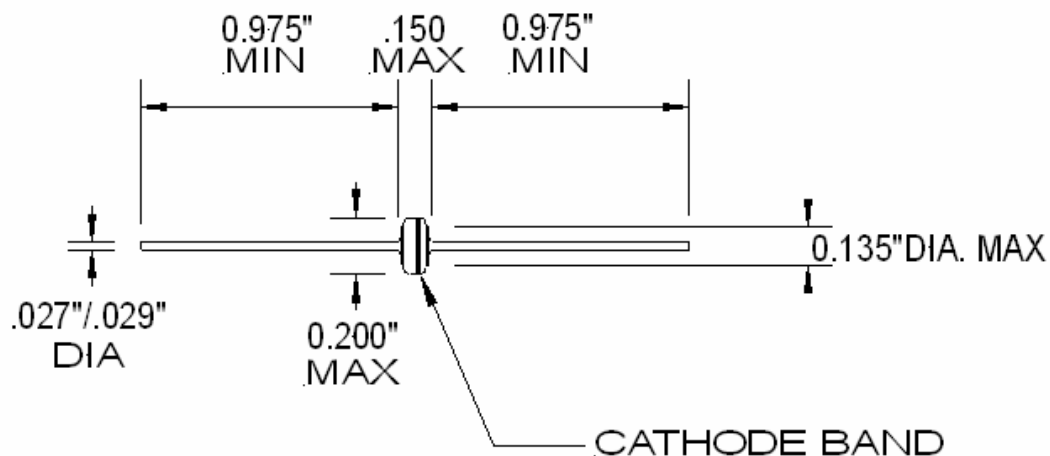
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Reliability

The UM9441 is consistent with Microsemi's reputation as a manufacturer of high reliability semiconductors. Microsemi is equipped to perform JAN type testing, base-lining and documental conformance to a wide range of reliability testing. This commitment to reliability has enabled Microsemi to be a qualified supplier of semiconductor devices to many high-reliability programs such as:

APOLLO
DRAGON
HAWK
MARINER

MINUTEMAN
SPRINT
TRIDENT
VIKING





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NOTES:

www.Microsemi.com

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